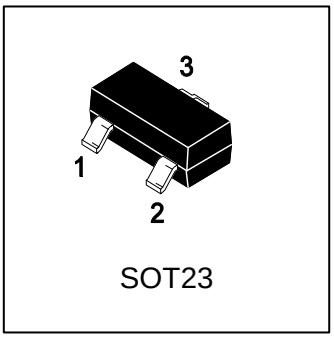
# L2SC2411KRLT1G
# S-L2SC2411KRLT1G

General Purpose Transistors NPN Silicon

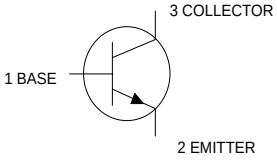



## 1. FEATURES

- We declare that the material of product compliance with RoHS requirements and Halogen Free.
- S- prefix for automotive and other applications requiring unique site and control change requirements; AEC-Q101 qualified and PPAP capable.

## 2. DEVICE MARKING AND ORDERING INFORMATION

| Device | Marking | Shipping |
|---|---|---|
| L2SC2411KRLT1G | CR | 3000/Tape&Reel |
| L2SC2411KRLT3G | CR | 10000/Tape&Reel |




## 3. MAXIMUM RATINGS(Ta = 25ºC)

| Parameter | Symbol | Limits | Unit |
|---|---|---|---|
| Collector–Emitter Voltage | VCEO | 32 | Vdc |
| Collector–Base Voltage | VCBO | 40 | Vdc |
| Emitter–Base Voltage | VEBO | 5 | Vdc |
| Collector Current — Continuous | IC | 500 | mAdc |

## 4. THERMAL CHARACTERISTICS

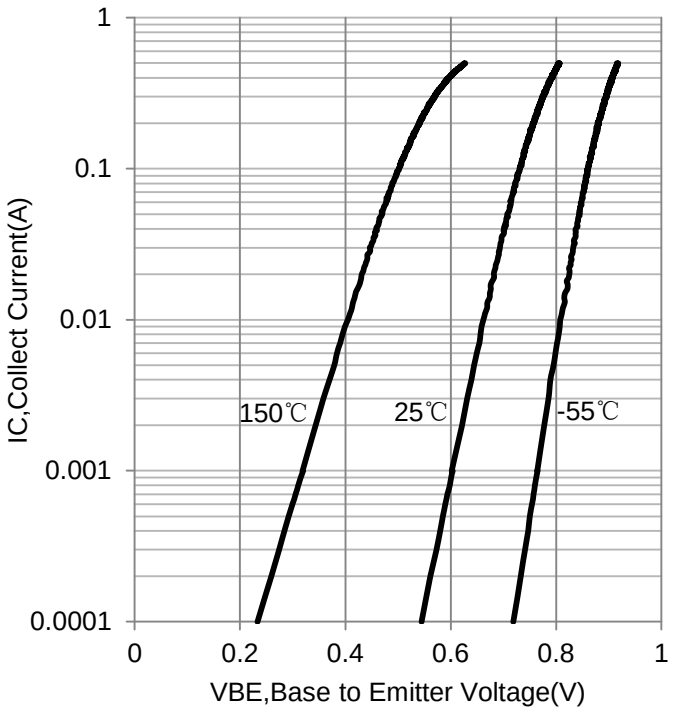
| Parameter | Symbol | Limits | Unit |
|---|---|---|---|
| Total Device Dissipation,<br>FR−5 Board (Note 1) @ TA = 25ºC<br>Derate above 25ºC | PD | <br>225<br>1.8 | <br>mW<br>mW/ºC |
| Thermal Resistance,<br>Junction–to–Ambient(Note 1) | RΘJA | 556 | ºC/W |
| Junction and Storage temperature | TJ,Tstg | −55~+150 | º C |

1. FR–5 = 1.0×0.75×0.062 in.

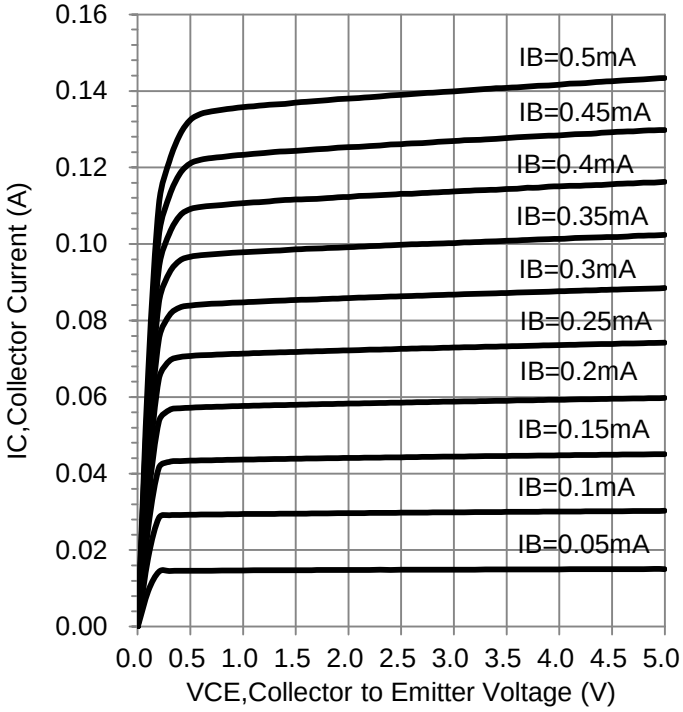
## 5. ELECTRICAL CHARACTERISTICS (Ta= 25°C)

| Characteristic | Symbol | Min. | Typ. | Max. | Unit |
|---|---|---|---|---|---|
| Collector–Emitter Breakdown Voltage (IC = 1 mAdc, IB = 0) | VBR(CEO) | 32 | - | - | V |
| Collector–Base Breakdown Voltage (IC = 100 μAdc, IE = 0) | VBR(CBO) | 40 | - | - | V |
| Emitter–Base Breakdown Voltage (IE = 100 μAdc, IC = 0) | VBR(EBO) | 5 | - | - | V |
| Collector Cutoff Current (VCB = 20 Vdc, IE = 0) | ICBO | - | - | 1 | μA |
| Emitter Cutoff Current (VEB = 4.0 Vdc, IC = 0) | IEBO | - | - | 1 | μA |
| DC Current Gain (IC = 100 mAdc, VCE = 3.0 Vdc) | HFE | 180 | - | 390 | |
| Collector–Emitter Saturation Voltage (IC = 500 mAdc, IB = 50 mAdc) | VCE(sat) | - | - | 0.4 | V |
| Base–Emitter Saturation Voltage (IC = 500 mAdc, IB = 50 mAdc) | VBE(sat) | - | - | 1.2 | V |
| Current–Gain — Bandwidth Product (IE = -20mAdc, VCE=5Vdc, f = 100MHz) | fT | - | 250 | - | MHz |
| Output Capacitance (VCB = 10 Vdc, IE = 0, f = 1.0 MHz) | Cob | - | 6 | - | pF |

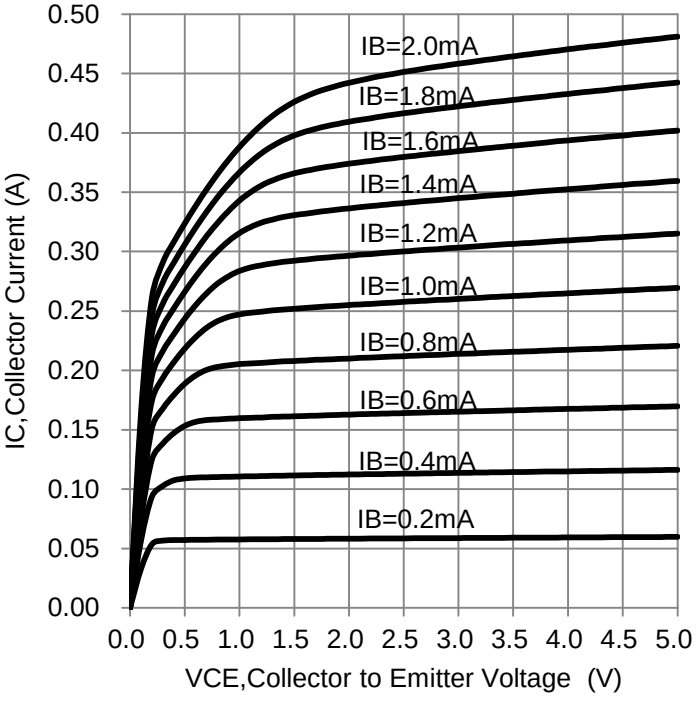
## 6. ELECTRICAL CHARACTERISTICS CURVES



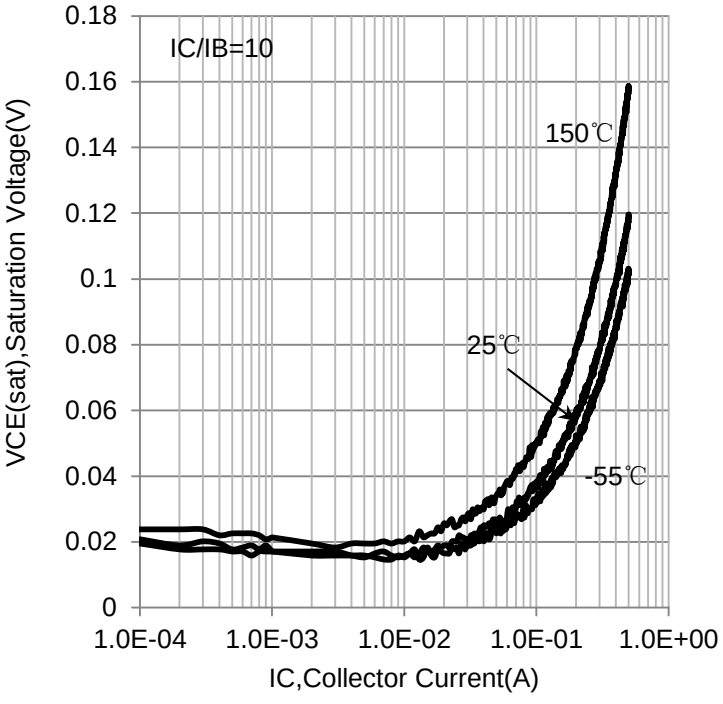

IC vs. VBE




IC vs. VCE

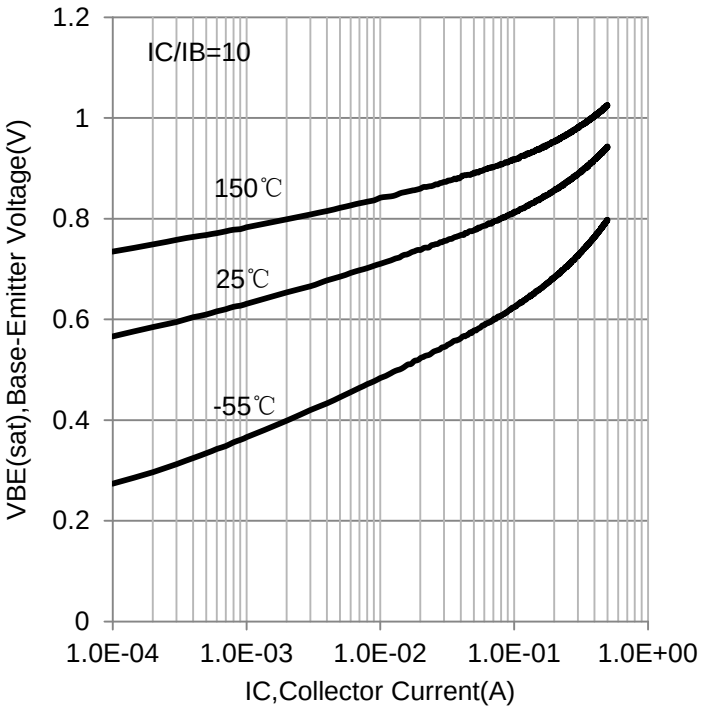



IC vs. VCE

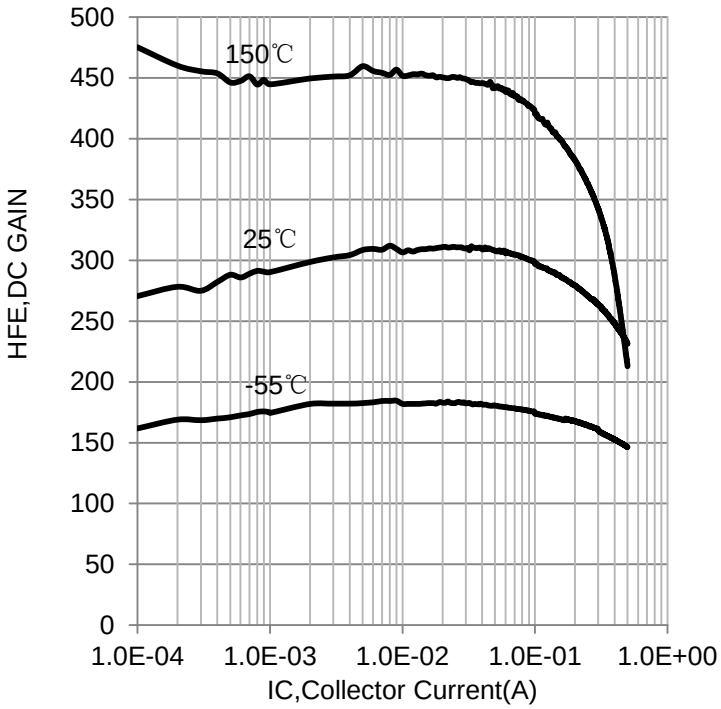



VCE(sat) vs. IC

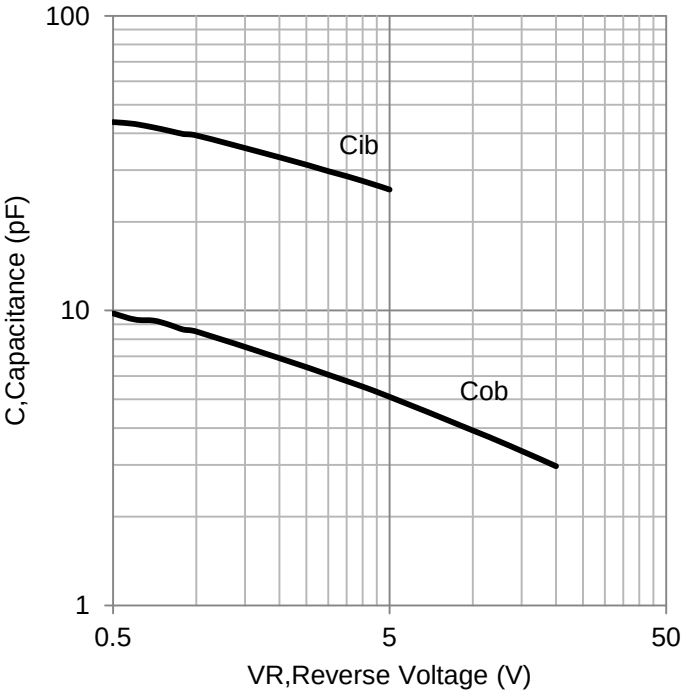
## 6. ELECTRICAL CHARACTERISTICS CURVES(Con.)




VBE(sat) vs. IC



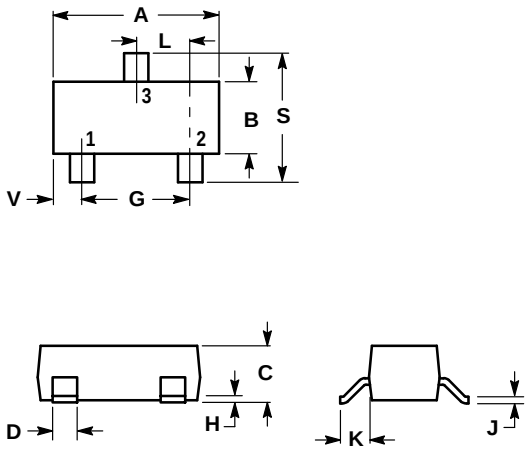

DC Current Gain vs. IC




Capacitance

## 7.OUTLINE AND DIMENSIONS

### SOT-23



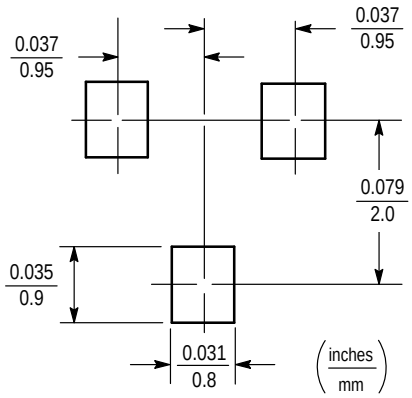

NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.

| DIM | INCHES | | MILLIMETERS | |
|---|---|---|---|---|
| | MIN | MAX | MIN | MAX |
| A | 0.1102 | 0.1197 | 2.80 | 3.04 |
| B | 0.0472 | 0.0551 | 1.20 | 1.40 |
| C | 0.0350 | 0.0440 | 0.89 | 1.11 |
| D | 0.0150 | 0.0200 | 0.37 | 0.50 |
| G | 0.0701 | 0.0807 | 1.78 | 2.04 |
| H | 0.0005 | 0.0040 | 0.013 | 0.100 |
| J | 0.0034 | 0.0070 | 0.085 | 0.177 |
| K | 0.0140 | 0.0285 | 0.35 | 0.69 |
| L | 0.0350 | 0.0401 | 0.89 | 1.02 |
| S | 0.0830 | 0.1039 | 2.10 | 2.64 |
| V | 0.0177 | 0.0236 | 0.45 | 0.60 |

PIN 1. BASE
2. EMITTER
3. COLLECTOR

## 8.SOLDERING FOOTPRINT



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